

TITLE OF THE INVENTION

ANODIZING APPARATUS AND METHOD AND POROUS SUBSTRATE

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BACKGROUND OF THE INVENTION

The present invention relates to an anodizing apparatus and method of anodizing a substrate to be processed in an electrolytic solution, and a porous substrate manufactured by the apparatus and method.

Porous silicon was found by A. Uhler and D.R. Turner who were studying electropolishing of single-crystal silicon biased to a positive potential in an aqueous solution of hydrofluoric acid (to be abbreviated as HF hereinafter).

Later, to exploit the excellent reactivity of porous silicon, application to element isolation in which a thick insulating structure need be formed in manufacturing a silicon integrated circuit was examined, and a full isolation technology using a porous silicon oxide film (FIPOS: Full Isolation by Porous Oxidized Silicon) was developed (K. Imai, Solid State Electron 24, 159, 1981).

Recently, an applied technology to direct bonding in which a silicon epitaxial layer grown on a porous silicon substrate is bonded to an amorphous substrate or single-crystal silicon substrate via an oxide film has been



developed (Japanese Patent Laid-Open No. 5-21338).

As another application example, porous silicon which emits light by itself has received a great deal of attention as a so-called photoluminescence or electroluminescence material (Japanese Patent Laid-Open No. 6-338631).

Fig. 5 is a view showing the arrangement of an anodizing apparatus for manufacturing porous silicon by anodizing a silicon substrate, disclosed in Japanese Patent Laid-Open No. 60-94737.

10 This anodizing apparatus is constituted by arranging anodizing tanks 1802a and 1802b consisting of Teflon (trade mark of du Pont in U.S.A) having an HF resistance to sandwich a silicon substrate 1801. The anodizing tanks 1802a and 1802b have platinum electrodes 1803a and 1803b,
15 respectively.

The anodizing tanks 1802a and 1802b have grooves in side walls contacting the silicon substrate 1801, and O-rings 1804a and 1804b of fluororubber are fitted in these grooves, respectively. The anodizing tanks 1802a and 1802b and the
20 silicon substrate 1801 are sealed by the O-rings 1804a and 1804b, respectively. The sealed anodizing tanks 1802a and 1802b are filled with HF solutions 1805a and 1805b, respectively.

In these anodizing tanks, the silicon substrate does
25 not come into direct contact with the metal electrodes and is hardly contaminated by the metal electrodes. However,



since the silicon substrate to be anodized is sealed by the O-rings on its upper and lower surfaces, unanodized portions remain in the peripheral regions on the surfaces of the silicon substrate. In addition, since the silicon substrate
5 to be processed itself is directly set and integrated with the anodizing tanks, the silicon substrate cannot be quickly exchanged.

To solve these problems, an anodizing apparatus which supports a silicon substrate at its side surface (beveling)
10 regions has been developed (Japanese Patent Laid-Open No. 5-198556). This anodizing apparatus can anodize all surface regions of the substrate while preventing contamination from the metal electrode. Additionally, in this anodizing apparatus, since a wafer to be processed is
15 fixed in a holder, and the holder is fixed in the anodizing tanks, i.e., the wafer is fixed in the anodizing tank in two steps, operability is largely improved as compared to the conventional apparatus which directly fixes a wafer in the anodizing tank to integrate the wafer with the anodizing
20 tank.

Another anodizing apparatus has been developed, in which a silicon substrate is arranged between a silicon substrate to be processed and a metal electrode, and the electrode component from the metal electrode is shielded by
25 the silicon substrate to prevent contamination due to the electrode component dissolved in the electrolytic solution



(Japanese Patent Laid-Open No. 5-86876).

As still another method of preventing contamination from the electrode, a method of directly fixing the electrode to a silicon substrate to be processed via another silicon
5 substrate has been developed (Japanese Patent Laid-Open No. 6-171076).

The anodizing apparatuses disclosed in Japanese Patent Laid-Open Nos. 5-198556, 5-86876, and 6-171076 are very practical because metal contamination rarely occurs, and all
10 surface regions of a substrate can be anodized.

However, an anodizing apparatus having higher productivity is desired. For example, the silicon substrate arranged between the silicon substrate to be processed and the metal electrode is anodized. The silicon substrate must
15 be discarded because it is in direct contact with the metal electrode or is contaminated by the metal component dissolved in the electrolytic solution, so the silicon material is wasted.

In the method of inserting the silicon substrate as an
20 intermediate substrate between the electrode and the silicon substrate to be processed, the intermediate substrate is also dipped in the electrolytic solution and anodized. Hence, the intermediate substrate must be frequently exchanged, and the silicon material is wasted.

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SUMMARY OF THE INVENTION

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The present invention has been made to solve the above problems, and has as its object to provide an anodizing apparatus and method capable of efficiently performing
5 anodizing while preventing wafer contamination.

It is another object of the present invention to provide a porous substrate manufactured by the apparatus and method.

In order to solve the above problems and achieve the above object, an anodizing apparatus according to the present
10 invention has the following arrangement.

There is provided an anodizing apparatus for anodizing a substrate to be processed in an electrolytic solution, comprising a process tank for storing the electrolytic solution, the process tank having an opening in a wall, a
15 negative electrode arranged in the process tank to oppose the opening, and a positive electrode contacting a surface of the substrate to be processed which is arranged to close the opening from an inside of the process tank, the surface being open outside the process tank through the opening.

20 A porous substrate according to the first aspect of the present invention has the following arrangement.

There is provided a porous substrate manufactured by the anodizing apparatus of any one of claims 1 to 14.

An anodizing method according to the present invention
25 has the following steps.

There is provided an anodizing method of anodizing a

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substrate to be processed in an electrolytic solution,
comprising the setting step of setting the substrate to be
processed inside a process tank having an opening on a wall
to close the opening, the supply step of supplying the
5 electrolytic solution into the process tank, the contacting
step of bringing a positive electrode into contact with a
portion of the substrate to be processed, which is open
outside the process tank through the opening, and the process
step of flowing a current between the positive electrode and
10 a negative electrode arranged to oppose the substrate to be
processed in the process tank to anodize the substrate to
be processed.

A porous substrate according to the second aspect of
the present invention has the following structure.

15 There is provided a porous substrate manufactured by
the anodizing method of any one of claims 16 to 27.

Other objects and advantages besides those discussed
above shall be apparent to those skilled in the art from the
description of a preferred embodiment of the invention which
20 follows. In the description, reference is made to
accompanying drawings, which form a part hereof, and which
illustrate an example of the invention. Such example,
however, is not exhaustive of the various embodiments of the
invention, and therefore reference is made to the claims
25 which follow the description for determining the scope of
the invention.

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BRIEF DESCRIPTION OF THE DRAWINGS

Figs. 1A to 1F are views showing the steps in
5 manufacturing a semiconductor substrate;

Fig. 2 is a plan view showing the overall arrangement
of an anodizing apparatus according to an embodiment;

Fig. 3 is an enlarged sectional view of an anodizing
tank portion in Fig. 2;

10 Fig. 4 is a flow chart for explaining operation of the
anodizing apparatus; and

Fig. 5 is a view showing the arrangement of a
conventional anodizing apparatus.

15 DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT

An anodizing apparatus according to an embodiment of
the present invention will be described below. Before the
description, an embodiment of a method of manufacturing a
20 semiconductor substrate using the anodizing apparatus in
some steps will be described.

Figs. 1A to 1F are views showing a method of
manufacturing a semiconductor substrate. This will be
briefly described. In this manufacturing method, a first
25 substrate prepared by forming a porous silicon layer on a
single-crystal silicon substrate, a non-porous layer on the



porous silicon layer, and preferably an insulating film on the non-porous layer is bonded to an independently prepared second substrate via the insulating film. After this, the single-crystal silicon substrate is removed from the lower
5 surface of the first substrate, and the porous silicon layer is etched, thereby manufacturing a semiconductor substrate.

The method of manufacturing a semiconductor substrate will be described in more detail with reference to Figs. 1A to 1F.

10 First, a single-crystal Si substrate 51 for forming a first substrate is prepared, and a porous Si layer 52 is formed on the major surface (Fig. 1A). The porous Si layer 52 can be formed by processing the major surface of the single-crystal substrate 51 by the anodizing apparatus of the
15 embodiment to be described later.

At least one non-porous layer 53 is formed on the porous Si layer 52 (Fig. 1B). As the non-porous layer 53, a single-crystal Si layer, a poly-Si layer, an amorphous Si layer, a metal layer, a semiconductor compound layer, a
20 superconductor layer is suitable. A device structure such as a MOSFET may be formed in the non-porous layer 53.

An SiO_2 layer 54 is formed on the non-porous layer 53, and the resultant structure is preferably used as the first substrate (Fig. 1C). This SiO_2 layer 54 is applicable
25 because when the first substrate is bonded to a second substrate 55 in the subsequent step, the interface level of



the bonding interface can be separated from the active layer.

Subsequently, the first substrate is brought into contact with the second substrate 55 at room temperature via the SiO_2 layer 54 (Fig. 1D). After this, anode bonding, pressing, heat treatment as needed, or a combination thereof may performed to firmly bond the substrates.

When a single-crystal Si layer is formed as the non-porous layer 53, the first substrate is preferably bonded to the second substrate 55 after the SiO_2 layer 54 is formed on the surface of the single-crystal Si layer by, e.g., thermal oxidation.

As the second substrate 55, an Si substrate, a substrate obtained by forming an SiO_2 layer on an Si substrate, a transparent substrate consisting of silica glass, or a sapphire substrate is suitable. Any other substrate can be used as far as the second substrate 55 has a sufficiently flat surface to be bonded.

Fig. 1D shows a state wherein the first substrate and the second substrate are bonded via the SiO_2 layer 54. If the non-porous layer 53 or the second substrate does not consist of Si, the SiO_2 layer 54 need not be formed.

In bonding, an insulating thin plate may be inserted between the first substrate and the second substrate.

The first substrate is removed from the second substrate at the porous Si layer 52 (Fig. 1E). To remove the first substrate, the first method using grinding, polishing, or



etching (the first substrate is discarded) or the second method of separating the first substrate from the second substrate at the porous layer 52 is used. In the second method, when the porous Si layer remaining on the separated
5 first substrate is removed, and the surface is planarized as needed, the substrate can be reused.

Subsequently, only the porous Si layer 52 is etched and removed while leaving the non-porous layer 53 (Fig. 1F).

Fig. 1F schematically shows a semiconductor substrate
10 obtained by the above manufacturing method. According to the manufacturing method, the non-porous layer 53 (e.g., a single-crystal Si layer) is formed flat and uniformly in the entire region on the surface of the second substrate 55.

When an insulating substrate is used as the second
15 substrate 55, the semiconductor substrate obtained by the above manufacturing method is very applicable to form an insulated electronic device.

An embodiment of an anodizing apparatus for obtaining a single-crystal substrate having a porous Si layer on the
20 surface, as shown in Fig. 1A, will be described next.

Formation of a porous silicon substrate by anodizing or formation of pores is performed in, e.g., an HF solution. It is known that the presence of holes is essential for this processing, and the reaction mechanism is estimated as
25 follows.

First, holes in the silicon substrate applied with an



electric field in the HF solution are induced on the surface on the negative electrode side. Consequently, the density of Si-H bonds compensating for the unbonded element on the surface becomes high. At this time, F ions in the HF solution on the negative electrode side nucleophilically attack the Si-H bonds to form Si-F bonds. By this reaction, H_2 molecules are generated, and simultaneously, one electron is emitted to the positive electrode side. Si-Si bonds near the surface weaken due to the polarization characteristics of Si-F bonds. This weak Si-Si bonds are attacked by HF or H_2O , so Si atoms on the surface become SiF_4 and are eliminated from the crystal surface. As a consequence, recessed portions are formed in the crystal surface. A field distribution (field concentration) for preferentially attracting holes is generated at this portion. This surface heterogeneity extends, so etching of silicon atoms continuously progresses along the electric field. The solution used for anodizing is not limited to the HF solution, and any other electrolytic solution can be used.

Fig. 2 is a plan view showing the overall arrangement of the anodizing apparatus of this embodiment.

Operation of an anodizing apparatus 100 is controlled by, e.g., a computer. Reference numeral 101 denotes a control panel. When a substrate carrier is placed on a loader 102, the loader 102 transfers the substrate to a single substrate conveyor robot 104. The wafer conveyor robot 104



removes substrates from the loader 102 one by one, conveys the substrate to an anodizing tank 103, and transfers the substrate to a robot 105. The robot 105 causes a holder in the anodizing tank 103 to chuck the received substrate. The
5 anodizing tank 103 can simultaneously support seven substrates. When seven substrates are stored in the anodizing tank 103, a positive electrode 11 moves in a direction indicated by an arrow A (details will be described later) and comes into contact with the seventh substrate.
10 After this, the anodizing tank 103 is filled with an electrolytic solution, and a voltage is applied across the positive electrode 11 and a negative electrode 2 arranged in the anodizing tank 103, thereby performing anodizing.

The anodized substrate is removed from the anodizing
15 tank 103 by the robot 105, mounted on a carrier in a washing tank 106, and washed.

When washing is complete, the substrate is conveyed to a drier 108 by a carrier conveyor robot 107 together with the carrier.

20 When drying by the drier 108 is complete, the substrate is conveyed by the carrier conveyor robot 107 again together with the carrier and transferred to an unloader 109 for unloading the substrate.

Fig. 3 is an enlarged sectional view showing the
25 anodizing tank 103 in Fig. 2. The anodizing tank 103 can store seven silicon substrates in fact, though Fig. 3 shows

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a simple structure for storing two silicon substrates for the descriptive convenience.

Referring to Fig. 3, reference numerals 6 and 7 denote single-crystal silicon substrates (wafers). Generally,
5 since the presence of holes is important for anodizing, a p-type silicon substrate is suitable. However, even an n-type silicon substrate can be used by prompting generation of holes by light irradiation or the like.

The positive electrode 11 and negative electrode 2 are
10 preferably formed from a chemically stable platinum material. The positive electrode 11 and negative electrode 2 are connected to a power supply 4.

A conductive partition 10 is fixed to the positive electrode 11. The positive electrode 11 contacts the silicon
15 substrate 7 via the conductive partition 10. The conductive partition 10 prevents the silicon substrate from being contaminated by the electrode material when the positive electrode 11 comes into direct contact with the silicon substrate 7. In this embodiment, a silicon substrate of the
20 same material as that of the silicon substrate 7 to be anodized is used. It is supposed that when the substrates are made of the same silicon material, the silicon substrate 7 to be processed is not contaminated by the silicon material of the conductive partition 10. The conductive partition 10 is
25 preferably formed from a material having a low resistivity not to impede current flow from the positive electrode 11



to the silicon substrate 7. In this sense, silicon is a preferable material. However, any material other than silicon can be used as the material of the conductive partition 10 as far as it has a low resistivity and does not
5 contaminate the silicon substrate 7 to be processed.

To fix the conductive partition 10 on the positive electrode 11, a plurality of holes having a diameter of about 5 mm or less are formed in the platinum plate forming the positive electrode 11, and these holes are filled with an
10 adhesive to directly bond the conductive partition 10 to a supporter 14 of the positive electrode 11. Alternatively, the conductive partition 10 may be vacuum-chucked using these holes.

The conductive partition 10 and positive electrode 11
15 preferably have the same area. However, the diameter of the positive electrode 11 may be smaller than the conductive partition 10 by about 20 mm. The conductive partition 10 preferably has a thickness similar to that of the silicon substrate 7 to be processed in fact because when the
20 conductive partition 10 is thin, the field distribution becomes nonuniform, and when the conductive partition 10 is thick, the electrical resistance increases. The sizes of the conductive partition 10 and positive electrode 11 are preferably as close to the silicon substrate 7 to be processed
25 as possible.

The positive electrode 11 is driven in a direction



indicated by an arrow B by a driving source 15 such as an air cylinder or a plunger. The positive electrode 11 is moved to a position where the positive electrode 11 comes into contact with the silicon substrate 7 and a position separated
5 from the silicon substrate 7. A compression spring 17 is inserted between a shaft 16 of the driving source 15 and the supporter 14. When the shaft 16 projects from the driving source 15, the positive electrode 11 is pressed against the silicon substrate 7 by the biasing force of the compression
10 spring 17. The biasing force of the compression spring 17 is set not to deform the silicon substrate 7.

To determine whether the positive electrode 11 is in contact with the silicon substrate 7, a signal for causing the driving source 15 to project the shaft 16 is detected
15 to determine that the positive electrode 11 is in contact with the silicon substrate 7, or a current is actually flowed between the positive electrode 11 and the negative electrode 2 after supply of an electrolytic solution (HF) 3 into the anodizing tank 103, and electrical connection between the
20 positive electrode 11 and the negative electrode 2 is detected for determination.

Holders 5 for supporting the silicon substrates 6 and 7 are made of, e.g., ethylene tetrafluoride (tradename: Teflon) or a material having HF resistance. The holder 5 has
25 an opening having a circle or circular shape and a diameter smaller than that of the silicon substrate to be supported



(a circular shape includes a shape close to a circle hereinafter).

An annular groove is formed at the peripheral portion of the opening of each holder 5, and an O-ring 8 having HF resistance is fitted in this groove. Air is exhausted from a hole (not shown) formed at the bottom portion of this groove, thereby chucking and fixing the silicon substrate 6 or 7 on the holder 5 via the O-ring 8. The holder 5 also has, at its lower portion, a seal member 9 for isolating the electrolytic solution 3.

Chambers 20, 21, 22 of an anodizing tank main body 1 are completely isolated by the O-rings 8 and seal members 9 via the silicon substrates 6 and 7. The electrolytic solution 3 supplied to the two chambers 20 and 21 of the anodizing tank main body 1 does not leak to the chamber 22 located at the right end of the anodizing tank main body 1. Since the conductive partition 10 neither contacts the electrolytic solution 3 nor is anodized, the conductive partition 10 need not be exchanged for a long time, so the silicon material is prevented from being wasted.

Operation of the anodizing apparatus having the above arrangement will be described next with reference to Figs. 2 and 3 and the flow chart of Fig. 4.

A carrier on which silicon substrates are mounted is set in the loader 102 (step S2). Each silicon substrate is conveyed from the loader 102 to the anodizing tank 103 by

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the robots 104 and 105 until seven silicon substrates are
chucked by the holder 5 (steps S4 to S10).

The driving source 15 is driven to bring the positive
electrode 11 into contact with the silicon substrate 7 via
5 the conductive partition 10 (step S12).

The electrolytic solution 3 is supplied to the anodizing
tank 103 and circulated, and the power supply 4 is turned
on to perform anodizing (steps S14 to S18).

The electrolytic solution is discharged from a
10 discharge port (not shown) formed in the anodizing tank 103,
and pure water is supplied to the anodizing tank 103 (steps
S20 to S22). With this operation, the silicon substrates are
roughly cleaned.

The pure water is discharged from the anodizing tank
15 103, and the positive electrode 11 is separated from the
silicon substrate 7 (steps S24 to S26).

In this state, each silicon substrate is released and
moved to a carrier in the washing tank 106. This operation
is repeatedly performed for the seven silicon substrates
20 (steps S28 to S34).

Normally, 25 silicon substrates are stored in the
carrier supplied to the loader 102. It is determined whether
silicon substrates remain on the carrier on the loader (step
S36). If any silicon substrates remain, the process from
25 step S4 to step S36 is repeated. If it is determined in step
S36 that no silicon substrate remains on the carrier on the

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loader 102, anodizing of 25 silicon substrates is complete, so 25 anodized silicon substrates are stored on the carrier in the washing tank 106.

The anodized silicon substrates are washed, and the
5 washed silicon substrates are conveyed to the drier 108 by the robot 107 together with the carrier and dried (steps S38 to S42).

The dried silicon substrates are conveyed to the
unloader 109 by the robot 107 together with the carrier and
10 unloaded (step S44).

The empty carrier is set in the unloader 109, conveyed to the washing tank 106 by the robot 107, and sank in the washing tank 106.

Finally, a carrier storing new silicon substrates is
15 set in the loader 102, and the operation from step S2 to step S50 is repeated.

If it is determined in step S50 that no carriers storing new silicon substrates remain, the operation of the apparatus is ended.

20 As described above, according to the above embodiment, since the conductive partition 10 for preventing contamination of the silicon substrate is inserted between the positive electrode 11 and the silicon substrate 7, contamination of the silicon substrate due to the electrode
25 material can be prevented.

In addition, since the positive electrode 11 does not



contact the electrolytic solution, the conductive partition
10 is not anodized and can be repeatedly used, so the silicon
material can be prevented from being wasted.

The present invention can be applied to changes and
5 modifications of the above embodiment without departing the
spirit and scope of the invention.

As has been described above, according to the present
invention, an anodizing apparatus and method capable of
efficiently performing anodizing while preventing wafer
10 contamination are provided.

The present invention is not limited to the above
embodiments and various changes and modifications can be made
within the spirit and scope of the present invention.
Therefore, to apprise the public of the scope of the present
15 invention, the following claims are made.

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WHAT IS CLAIMED IS:

1. An anodizing apparatus for anodizing a substrate to be processed in an electrolytic solution, comprising:
 - 5 a process tank for storing the electrolytic solution, said process tank having an opening in a wall;
 - a negative electrode arranged in said process tank to oppose the opening; and
 - a positive electrode contacting a surface of the
 - 10 substrate to be processed which is arranged to close the opening from an inside of said process tank, the surface being open outside said process tank through the opening.
2. The apparatus according to claim 1, wherein said process tank can support at least another substrate to be processed
- 15 between said negative electrode and the substrate to be processed and anodize the plurality of substrates to be processed at once.
3. The apparatus according to claim 1, further comprising moving means for moving said positive electrode close to or
- 20 away from the substrate to be processed.
4. The apparatus according to claim 3, wherein said moving means comprises a support member for supporting said positive electrode, a spring arranged between said positive electrode and said support member to elastically support said positive
- 25 electrode, and a driving source for moving said support member.

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5. The apparatus according to claim 4, wherein said driving source comprises an air cylinder.
6. The apparatus according to claim 5, wherein contact between said positive electrode and the substrate to be
5 processed is confirmed upon detecting a driving signal for said air cylinder.
7. The apparatus according to claim 4, wherein said driving source comprises a plunger.
8. The apparatus according to claim 7, wherein contact
10 between said positive electrode and the substrate to be processed is confirmed upon detecting a driving signal for said plunger.
9. The apparatus according to claim 3, wherein contact between said positive electrode and the substrate to be
15 processed is confirmed by filling said process tank with the electrolytic solution and detecting electrical connection between said positive electrode and said negative electrode.
10. The apparatus according to claim 3, wherein said positive electrode is made of a metal plate and comes into
20 contact with the substrate to be processed via an intermediate substrate made of a material which has a low electrical resistance and does not contaminate the substrate to be processed.
11. The apparatus according to claim 10, wherein said
25 intermediate substrate is made of the same material as that of the substrate to be processed.

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12. The apparatus according to claim 11, wherein the substrate to be processed and said intermediate substrate are made of single-crystal silicon.

13. The apparatus according to claim 11, wherein said
5 intermediate substrate has substantially the same size as that of the substrate to be processed.

14. The apparatus according to claim 1, wherein said positive electrode has substantially the same size as that of the substrate to be processed.

10 15. A porous substrate manufactured by the anodizing apparatus of claim 1.

16. An anodizing method of anodizing a substrate to be processed in an electrolytic solution, comprising:

the setting step of setting the substrate to be
15 processed inside a process tank having an opening on a wall to close the opening;

the supply step of supplying the electrolytic solution into the process tank;

the contacting step of bringing a positive electrode
20 into contact with a portion of the substrate to be processed, which is open outside the process tank through the opening; and

the process step of flowing a current between the positive electrode and a negative electrode arranged to
25 oppose the substrate to be processed in the process tank to anodize the substrate to be processed.

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17. The method according to claim 16, further comprising:
the first discharge step of discharging the
electrolytic solution from the process tank;
the cleaning step of supplying pure water into the
5 process tank to clean the substrate to be processed;
the second discharge step of discharging the pure water
from the process tank;
the separation step of separating the positive
electrode from the substrate to be processed; and
10 the removal step of removing the substrate to be
processed from the process tank.
18. The method according to claim 16, wherein the process
tank can support at least another substrate to be processed
between the negative electrode and the substrate to be
15 processed and anodize the plurality of substrates to be
processed at once.
19. The method according to claim 16, further comprising
the contacting step of, after the substrate to be processed
is set in the process tank, bringing the positive electrode
20 into contact with the substrate.
20. The method according to claim 19, wherein contact
between the positive electrode and the substrate to be
processed is confirmed upon detecting a driving signal for
an air cylinder as a driving source of the positive electrode.
- 25 21. The method according to claim 19, wherein contact
between the positive electrode and the substrate to be





processed is confirmed upon detecting a driving signal for a plunger as a driving source of the positive electrode.

22. The method according to claim 19, wherein contact between the positive electrode and the substrate to be
5 processed is confirmed by filling the process tank with the electrolytic solution and detecting electrical connection between the positive electrode and the negative electrode.

23. The method according to claim 19, wherein the positive electrode is made of a metal plate and comes into contact
10 with the substrate to be processed via an intermediate substrate made of a material which has a low electrical resistance and does not contaminate the substrate to be processed.

24. The method according to claim 23, wherein the
15 intermediate substrate is made of the same material as that of the substrate to be processed.

25. The method according to claim 23, wherein the substrate to be processed and the intermediate substrate are made of single-crystal silicon.

20 26. The method according to claim 23, wherein the intermediate substrate has substantially the same size as that of the substrate to be processed.

27. The method according to claim 16, wherein the positive electrode has substantially the same size as that of the
25 substrate to be processed.

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28. A porous substrate manufactured by the anodizing method of claim 16.

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